

ABSTRACT OF THE DISCLOSURE

A solid imaging device includes at least one pixel, the pixel including a photoelectric conversion section and a charge detection node which are coupled to or decoupled from each other via a transfer gate transistor, the charge detection node being coupled to or decoupled from a drain of a reset gate transistor via the reset gate transistor. After the reset gate resets a potential of the charge detection node, the transfer gate transistor is turned ON so as to allow a signal charge to be transferred from the photoelectric conversion section to the charge detection node, and thereafter a potential of the drain is changed from a HIGH state to a LOW state to a HIGH state while both of the transfer gate transistor and the reset gate transistor are maintained in an ON state.